

SI-PIN Photo Diode 400..1100nm

1 General

The RPOpto-Clamp is especially suitable for applications with standard 1mm plastic fiber optical cable. Pre-mounted with a high speed Si PIN photodiode the device is designed for visible to near infrared light detection with wideband characteristics at low bias, making it suitable for optical communications and other photometry. The RPOpto-Clamp is a good solution in data transmission systems with plastic fiber optical cable.

2 Applications

Due to the high speed, the good optical and mechanical features, this receiver may be used in many applications:

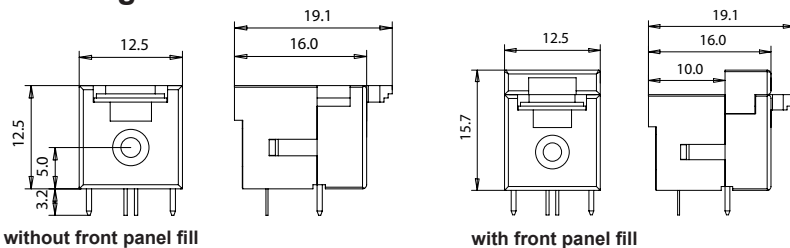
- Optical networks
- Industrial electronic
- Power electronic

3 Ordering Information

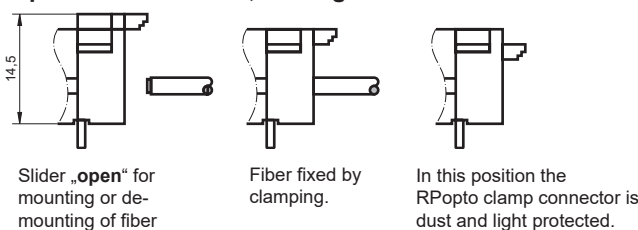
Style	Part Number
Photo diode	905EMPINKR003
Photo diode (with front panel fill)	905EMPINKR004

5 Technical Drawing

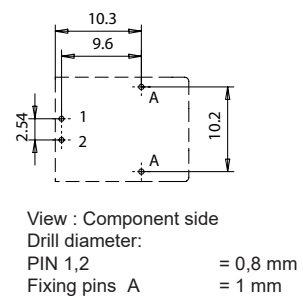
Housing



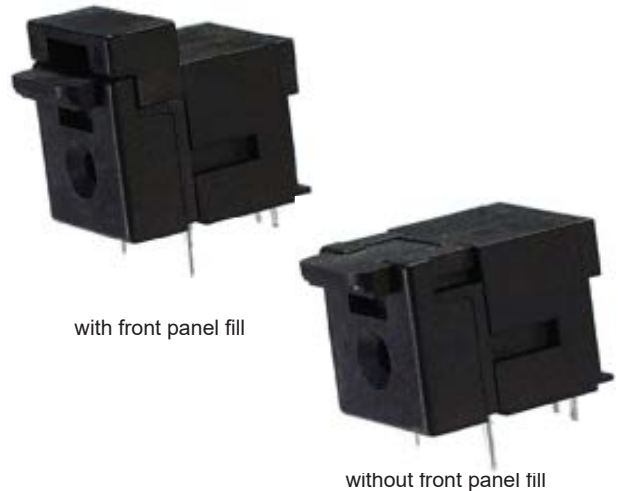
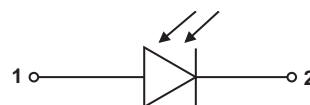
positions of sliders, locking mechanism



Drill drawing for PCB



Schematic diagram



Pic. 1 Fiber optic receiver

4 Features

- 400..1100nm PIN photodiode
- High sensitivity
- $t_r, t_f \leq 5ns$
- Suitable for all plastic optical fiber cables with an outside diameter of 2.2 mm and a fiber diameter of 1 mm
- Fast locking mechanism (manual control)
- Plastic housing
- Suitable for automatic assembly
- Reflow-/ wave soldering

Pic 2 Case drawing

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6 Maximum Ratings ($T_A=25^{\circ}\text{C}$) _____

Stresses beyond those listed under 'Maximum Ratings' may cause permanent damage to the device. Listed values are stress limits only and functional operation of the device at these conditions is not recommended. Exposure to maximum rating conditions for extended periods may affect the device reliability.

Parameter	Value	Unit
Operating temperature	-40 ... +100	°C
Storage temperature		
Soldering temperature: 1.) 2mm from case, $t \leq 10\text{s}$; 2.) max. 10s at max. 5s contact time per wave	260	°C
Reverse voltage	20	V
	50 at $t \leq 2\text{min}$	
Power dissipation	150	mW
ESD withstand voltage	2	kV

7 Technical Data ($T_A=25^{\circ}\text{C}$) _____

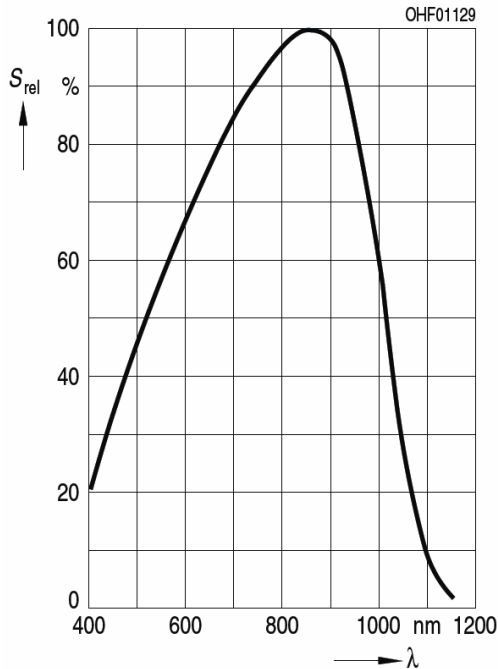
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Spectral range of sensitivity	$\lambda_{10\%}$		400		1100	nm
Wavelength of max sensitivity	$\lambda_{S_{max}}$			850		
Half angle	φ			75		°deg.
Dark current	I_R	$V_R=20\text{V}$		1	5	nA
Spectral sensitivity of the chip	S_A	$\lambda=850\text{nm}$		0.62		A/W
Open-circuit voltage	V_O	$E_V=1000\text{lx}$; Std. Light A	300	350		mV
Short-circuit current	I_{SC}	$E_V=1000\text{lx}$; Std. Light A		9.3		μA
Rise and fall time	t_r	$V_R = 20 \text{ V}; R_L = 50 \Omega;$ $\lambda = 850 \text{ nm}$		0.005		μs
	t_f					
Forward voltage	V_F	$I_F = 100 \text{ mA}; E = 0$		1.3		V
Capacitance	C_O	$V_R = 0 \text{ V}; f = 1 \text{ MHz}; E = 0$		11		pF
Temperature coefficient	TC_V	Voltage		-2.6		mV/K
	TC_I	Short-circuit current Std. Light A		0.18		%/K



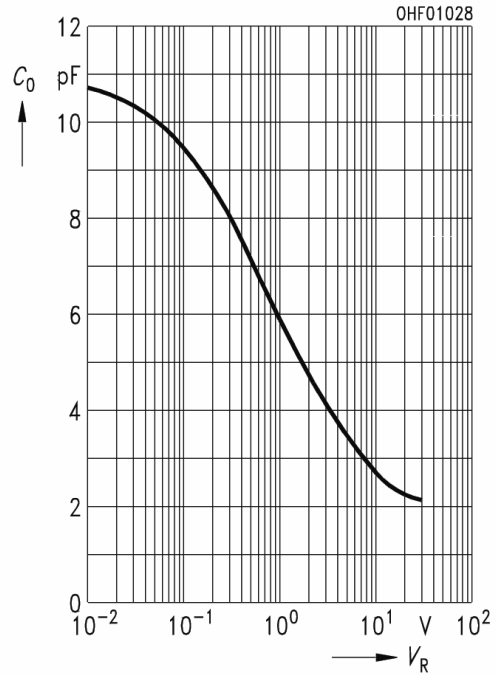
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8 Characteristics

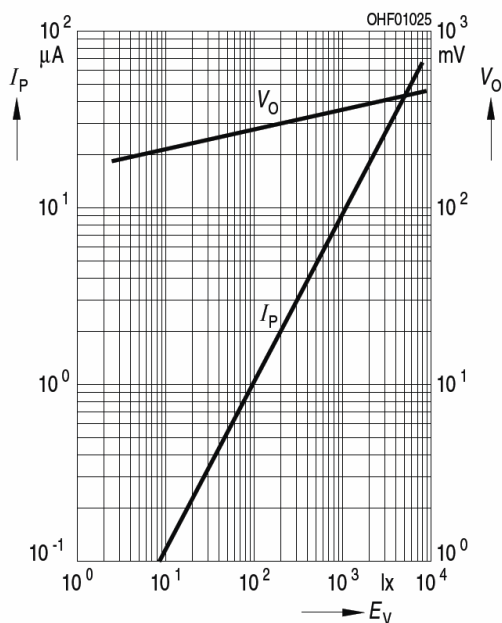
Relative Spectral Sensitivity



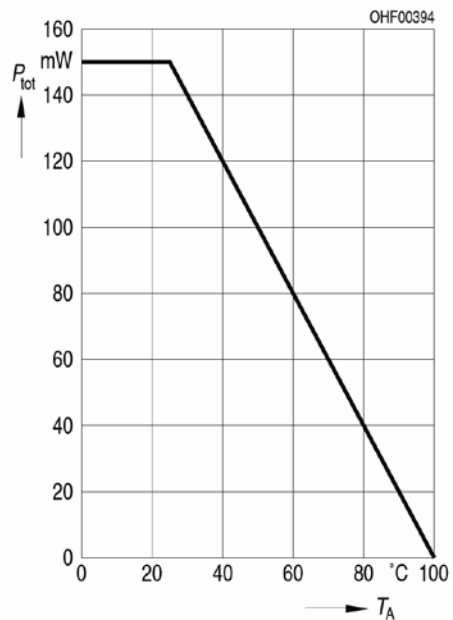
Capacitance



$I_P (V_R = 5 V) / V_O = f(E_V)$



$P_{tot} = f(T_A)$



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